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(54) Title: NON-VOLATILE MEMORY WITH RESISTIVE ACCESS COMPONENT

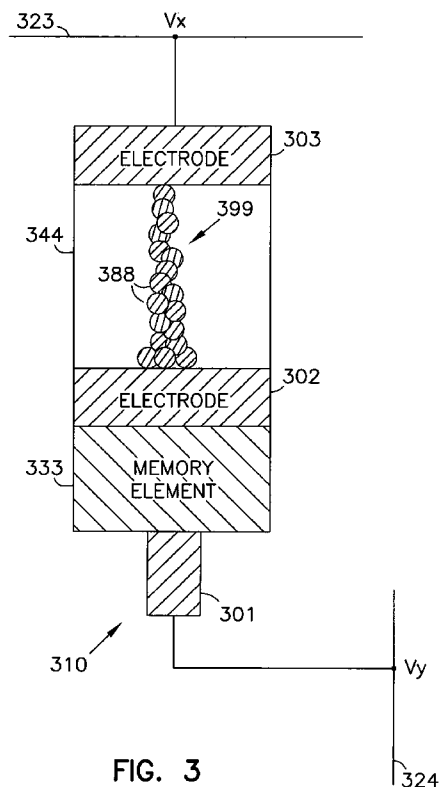


FIG. 3

(57) Abstract: Some embodiments include apparatus and methods having a memory element configured to store information and an access component configured to allow conduction of current through the memory element when a first voltage difference in a first direction across the memory element and the access component exceeds a first voltage value and to prevent conduction of current through the memory element when a second voltage difference in a second direction across the memory element and the access component exceeds a second voltage value, wherein the access component includes a material excluding silicon.

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